

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/700,466	11/05/2003	Tadahiro Ohmi	108390-00056	8803
4372	7590 11/15/2006		EXAMINER	
ARENT FO		TRAN, THIEN F		
1050 CONN SUITE 400	IECTICUT AVENUE, N.	W.	ART UNIT PAPER NUMBER	
	TON, DC 20036		2811	
•			DATE MAILED: 11/15/200	6

Please find below and/or attached an Office communication concerning this application or proceeding.

			3/
	Application No.	Applicant(s)	
	10/700,466	OHMI, TADAHIRO	
Office Action Summary	Examiner	Art Unit	
	Thien F. Trạn	2811	
The MAILING DATE of this communication appeared for Reply	pears on the cover sheet	with the correspondence address	
A SHORTENED STATUTORY PERIOD FOR REPL WHICHEVER IS LONGER, FROM THE MAILING D - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statut Any reply received by the Office later than three months after the mailin earned patent term adjustment. See 37 CFR 1.704(b).	NATE OF THIS COMMUN 136(a). In no event, however, may will apply and will expire SIX (6) Mile, cause the application to become	IICATION. a reply be timely filed DNTHS from the mailing date of this communication ABANDONED (35 U.S.C. § 133).	
Status			
1) ☐ Responsive to communication(s) filed on 29 A 2a) ☐ This action is FINAL . 2b) ☐ This 3) ☐ Since this application is in condition for alloware closed in accordance with the practice under A	s action is non-final. ance except for formal ma		is
Disposition of Claims			
4) ⊠ Claim(s) 8-12 and 14-16 is/are pending in the 4a) Of the above claim(s) 8-12,14 and 15 is/ar 5) □ Claim(s) is/are allowed. 6) ⊠ Claim(s) 16 is/are rejected. 7) □ Claim(s) is/are objected to. 8) □ Claim(s) are subject to restriction and/or	e withdrawn from consid	eration.	
Application Papers	,		
9) The specification is objected to by the Examina 10) The drawing(s) filed on is/are: a) acc Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the E	cepted or b) objected to drawing(s) be held in abey ction is required if the drawing.	ance. See 37 CFR 1.85(a). ng(s) is objected to. See 37 CFR 1.121	(d).
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documen 2. Certified copies of the priority documen 3. Copies of the certified copies of the priority application from the International Burea * See the attached detailed Office action for a list	nts have been received. Its have been received in brity documents have been received in the law (PCT Rule 17.2(a)).	Application No en received in this National Stage	
Attachment(s)			
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date	Paper N	w Summary (PTO-413) lo(s)/Mail Date of Informal Patent Application	

Application/Control Number: 10/700,466

Art Unit: 2811

DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claim 16 is rejected under 35 U.S.C. 102(b) as being anticipated by Hirayama et al. (Low-Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High-Density Krypton Plasma).

Hirayama et al. discloses a MOS transistor having a silicon semiconductor layer (Epi n-type Si{100}) that inherently has source and drain regions on both sides of a channel region, a silicon oxide film formed on said silicon semiconductor portion and a gate electrode (n⁺ poly Si) formed on said silicon oxide film, wherein said silicon oxide film contains Kr. Hirayama et al. further discloses the silicon oxide film grown by Kr/O2 mixed high-density is used to replace conventional thermally grown silicon oxide film (without Kr); therefore, it is inherent that a threshold voltage of the MOS transistor is substantially equal to that of an MOS transistor having a silicon oxide film without Kr.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thien F. Tran whose telephone number is (571) 272-1665. The examiner can normally be reached on 8:30AM - 5:00PM Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Richard Elms can be reached on (571) 272-1869. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Thien F Tran
Primary Examiner
Art Unit 2811

tt November 9, 2006